

Form PTO-1449 (Modified)
 PATENTS AND PUBLICATIONS
 FOR APPLICANT'S INFORMATION
 DISCLOSURE STATEMENT
 Use several sheets if necessary



ATTY. DOCUMENT NO.
 83175
 APPLICANT
Tak Kin Chu et al.
 FILING DATE
May 9, 2001

SERIAL NO.
09/853,925
 GROUP ART UNIT
2813

REFERENCE DESIGNATION				U.S. PATENT DOCUMENTS			
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>EK</i>	AA	5,690,737	11/25/97	Santiago et al.	117	92	
↑	AB	5,695,810	12/9/97	Dubin et al.	427	96	
	AC	5,824,599	10/20/98	Schacham-Diamand et al.	438	678	
	AD	5,225,031	7/6/93	McKee et al.	156	612	
	AE	5,248,633	9/28/93	Morar et al.	437	196	
	AF	5,378,905	1/3/95	Nakamura	257	213	
	AC	5,482,003	1/9/96	McKee et al.	117	108	
	AH	5,569,538	10/29/96	Cho	428	427	
	AI	5,593,951	1/14/97	Himpfel	505	235	
	AJ	5,637,533	6/10/97	Choi	438	643	
	AK	5,670,420	9/23/97	Choi	437	189	
	AL	5,677,572	10/14/97	Hung et al.	257	750	
	AM	5,696,018	12/9/97	Summerfelt et al.	437	60	
	AN	5,753,040	5/19/98	Cho	117	106	
	AO	5,773,085	6/30/98	Inoue et al.	427	255.2	
	AP	5,824,590	10/20/98	New	438	393	
	AQ	4,291,327	9/22/81	Tsang	357	52	
	AR	4,550,331	10/29/85	Milano	357	24	
	AS	4,692,993	9/15/87	Clark et al.	437	53	
	AT	4,847,666	7/11/89	Heremans et al.	357	16	
	AU	4,915,746	4/10/90	Welsch	148	4	
	AV	5,124,762	6/23/92	Childs et al.	357	16	
	AW	5,151,168	9/29/92	Gilton et al.	205	123	
	AX	5,435,264	7/25/95	Santiago et al.	117	92	
	AY	5,391,517	2/21/95	Gelatos et al.	437	190	
	AZ	5,773,359	6/30/98	Mitchell et al.	438	614	
↓ <i>EK</i>	BA	2001/0035581	11/1/01	Stumborg et al.	257	751	

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EK Kuhn 2/19/04

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
ER	BB	851,483	7/1/98	EPO			Yes
ER	BC	881,673	12/2/98	EPO			Yes
ER	BD	2-266569	10/31/90	Japan			Abstract only
ER	BE	6-310509	11/4/94	Japan			Yes
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
<div style="border: 1px solid black; border-radius: 50%; padding: 5px; display: inline-block;"> PIPE JC88 JUL 16 2003 PATENT & TRADEMARK OFFICE </div>	BF	Chaudhari et al., "Calcium Fluoride thin films on GaAs(100) for possible metal-insulator-semiconductor applications", Appl. Phys. Lett., Vol. 62, No. 8, 22 Feb. 1993, pp. 852-854.					
	BG	Colbow et al., "Photoemission study of the formation of SrF ₂ /GaAs(100) and BaF ₂ /GaAs(100) interfaces", Physical Review B, Vol. 49, No. 3, 15 Jan. 1994, pp. 1750-1756.					
	BH	Chu et al., "The Role of Barium in the Heteroepitaxial Growth of Insulator and Semiconductors on Silicon", Mat. Res. Soc. Symp. Proc., Vol. 334, 1994, pp. 501-506.					
	BI	Stumborg et al., "Determination of growth mechanisms of MBE grown BaF ₂ on Si(100) by target angle dependence of RBS yields", Nucl. Instr. And Methods in Physics Res. B, Vol. 95, 1995, pp. 319-322.					
	BJ	Stumborg et al., "Growth and interfacial chemistry of insulating (100) barium fluoride on gallium arsenide", J. Appl. Phys., Vol. 77, No. 6, 15 March 1995, pp. 2739-2744.					
	BK	Stumborg et al., "Surface chemical state populations in the molecular beam epitaxy deposition of BaF ₂ on GaAs by x-ray photoelectron spectroscopy and heavy-ion backscattering spectroscopy", J. Vac. Sci. Technol., Vol. 14, No. 1, Jan./Feb. 1996, pp. 69-79.					
	BL	Chu et al., "Heteroepitaxial deposition of Group IIa fluorides on gallium arsenide", Mat. Sci. and Eng., Vol. B47, 1997, pp. 224-234.					
	BM	D. Gardner et al., "Encapsulated Copper Interconnection Devices using Sidewall Barriers", Proc. 8 th Int'l IEEE VLSI MVIC, June 1991, pp. 99-108.					
	BN	T. Wade, "Gas Dome Dielectric System Provides Unity-k Dielectric", Semiconductor Int'l, July 1999, 6 pages total.					
	BO	Abe et al., "Metal Base Transistor of In/Bi (Ba,Rb)O ₃ /SrTiO ₃ (Nb)", IEEE, Vol. 14, March 1993, pp. 100-102.					
	BP	S. M. Sze, "Semiconductor Devices Physics and Technology", 1985, pp. 208-210.					
	BQ	Truscott et al., "MBE growth of BaF ₂ /(Ga,In)(As,Sb) Structures", Journal of Crystal Growth, Vol. 81 (1987), pp. 552-556.					
	BR	Clemens et al., "Growth of BaF ₂ and of BaF ₂ /SrF ₂ layers on (001) oriented GaAs", J. Appl. Phys., Vol. 66, No. 4, 15 Aug. 1989, pp. 1680-1685.					
ER	BS	Hung et al., "Epitaxial growth of alkaline earth fluoride films on HF-treated Si and (NH ₄) ₂ S _x -treated GaAs without in situ cleaning", Appl. Phys. Lett., Vol. 60, No. 2, 13 Jan. 1992, pp. 201-203.					

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if reference considered whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

(Information Disclosure Statement - Section 9 PTO-1449 (Modified) [6-1] page 01 of 02)

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